

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

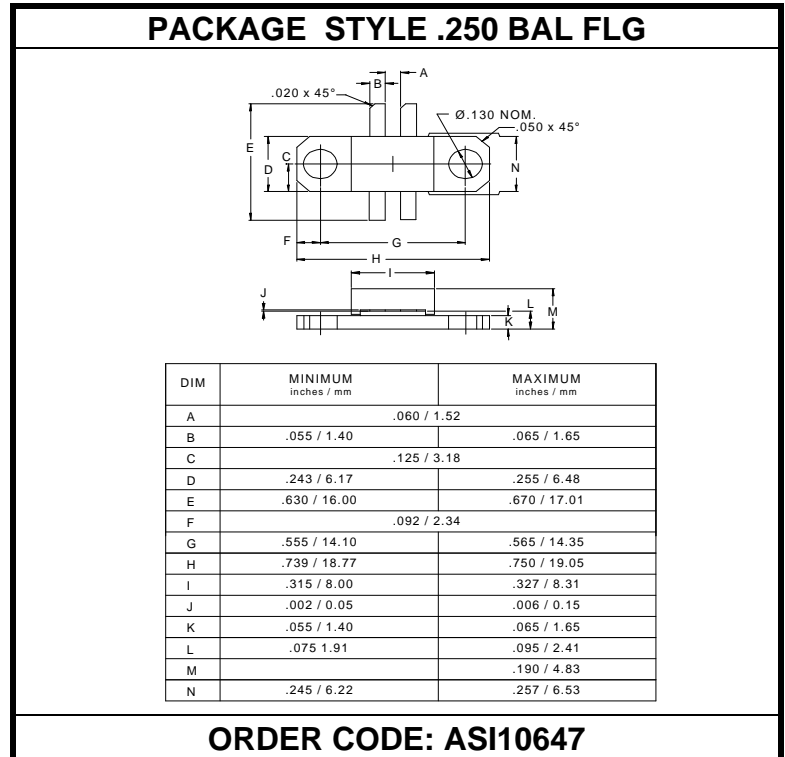
The **ASI TVU014** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	2 x 2.6 A
<b>V<sub>CB0</sub></b>	45 V
<b>V<sub>CEO</sub></b>	25 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	65 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	2.5 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 20 mA	45			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 40 mA	25			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5.0 mA	3.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 20 V    I <sub>C</sub> = 0.5 A	10		---	---
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 25 V    f = 1.0 MHz			20	<b>pF</b>
<b>P<sub>G</sub></b> <b>IMD<sub>1</sub></b>	V <sub>CE</sub> = 25 V    I <sub>C</sub> = 2 x 850 mA    f = 860 MHz P <sub>OUT</sub> = 14 W	8.5 -50			<b>dB</b> <b>dBc</b>